FAIRCHILD SEMICONDUCTOR®

March 2013

FDP61N20

N-Channel UniFET™ MOSFET

200 V, 61 A, 41 mΩ

Features

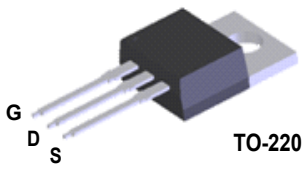
- $R_{DS(on)}$ = 41 mΩ (Max.) @ V_{GS} = 10 V, ID = 30.5 A
- Low Gate Charge (Typ. 58 nC)
- Low C_{rss} (Typ. 80 pF)
- 100% Avalanche Tested

Applications

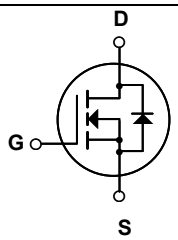
- PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFET™ MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220



Absolute Maximum Ratings

Symbol	Parameter		FDP61N20	Unit
V_{DSS}	Drain-Source Voltage		200	V
I_D	Drain Current	- Continuous (T_C = 25°C) - Continuous (T_C = 100°C)	61 38.5	A A
I_{DM}	Drain Current	- Pulsed (Note 1)	244	A
V_{GSS}	Gate-Source voltage		±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		1440	mJ
I_{AR}	Avalanche Current (Note 1)		61	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		41.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C) - Derate above 25°C	417 3.3	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FDP61N20	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP61N20	FDP61N20	TO-220	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	200	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	--	0.2	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 200V, V_{GS} = 0V V_{DS} = 160V, T_C = 125°C	-- --	-- --	1 10	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 30.5A	--	0.034	0.041	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40V, I_D =30.5A	--	44.5	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	--	2615	3380	pF
C_{oss}	Output Capacitance		--	645	840	pF
C_{rss}	Reverse Transfer Capacitance		--	80	120	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 100V, I_D = 61A R_G = 25Ω	--	40	90	ns
t_r	Turn-On Rise Time		--	215	440	ns
$t_{d(off)}$	Turn-Off Delay Time		--	125	260	ns
t_f	Turn-Off Fall Time	(Note 4)	--	170	350	ns
Q_g	Total Gate Charge	V_{DS} = 160V, I_D = 61A V_{GS} = 10V	--	58	75	nC
Q_{gs}	Gate-Source Charge		--	19	--	nC
Q_{gd}	Gate-Drain Charge	(Note 4)	--	24	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	61	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	244	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 61A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_S = 61A dI_F/dt =100A/μs	--	162	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.5	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 0.58mH, I_{AS} = 61A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. $I_{SD} \le$ 61A, di/dt ≤ 200A/μs, $V_{DD} \le BV_{DSS}$, Starting T_J = 25°C
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

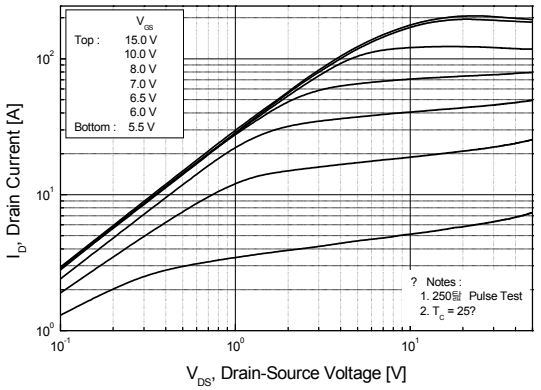


Figure 2. Transfer Characteristics

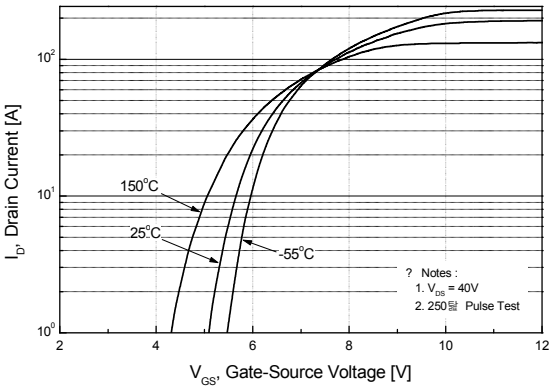


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

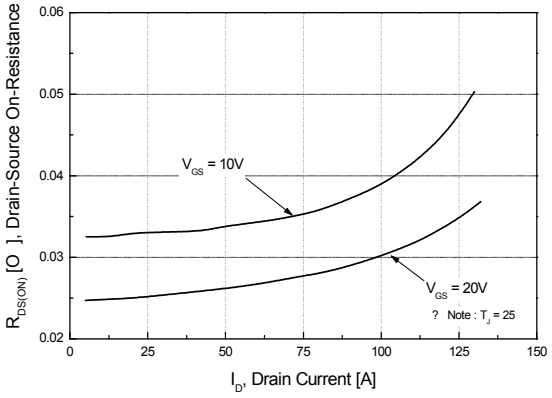


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

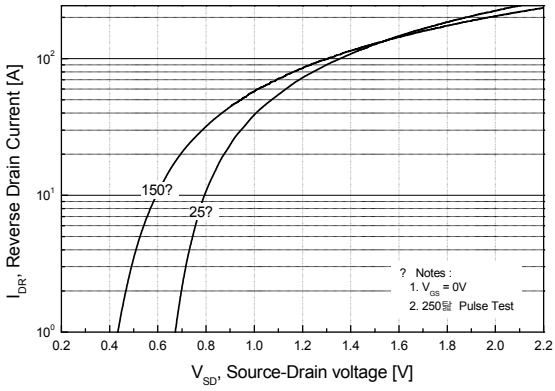


Figure 5. Capacitance Characteristics

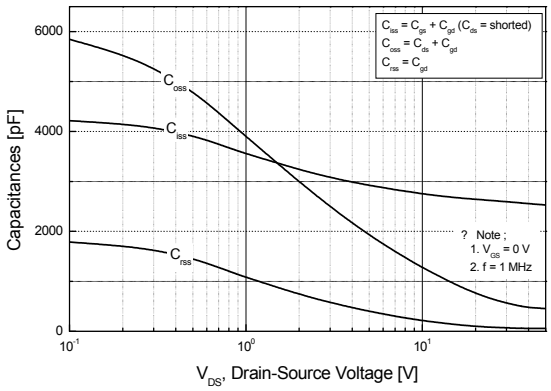
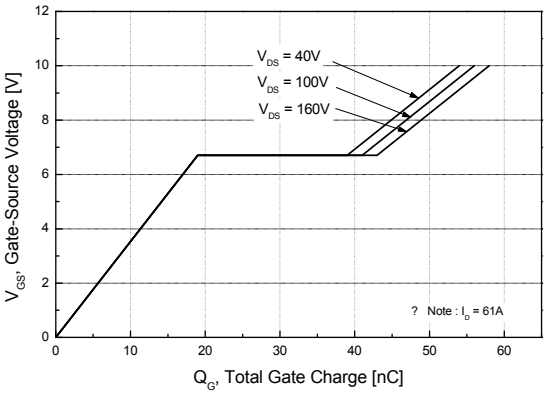


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

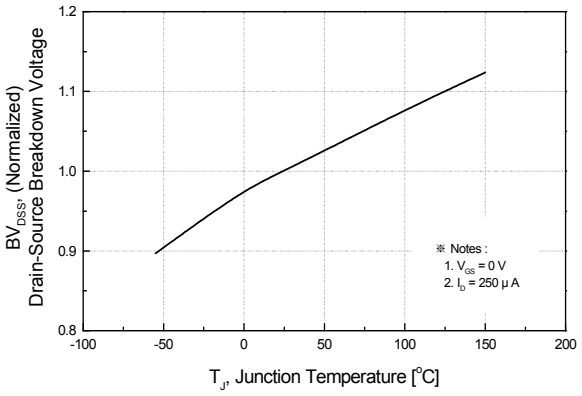


Figure 8. On-Resistance Variation vs. Temperature

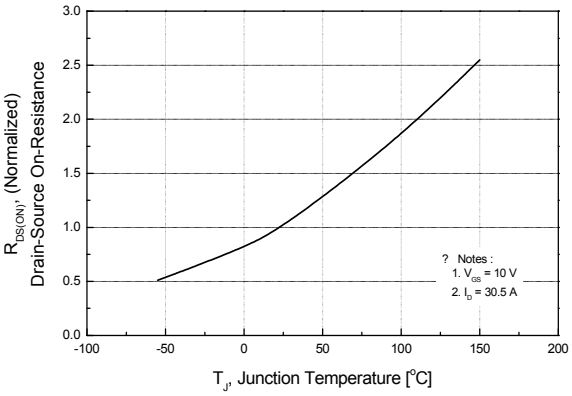


Figure 9. Safe Operating Area

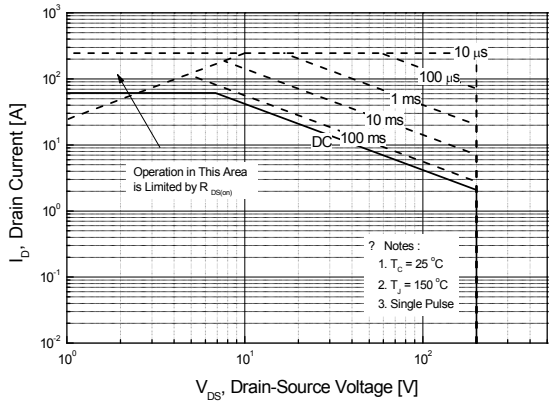


Figure 10. Maximum Drain Current vs. Case Temperature

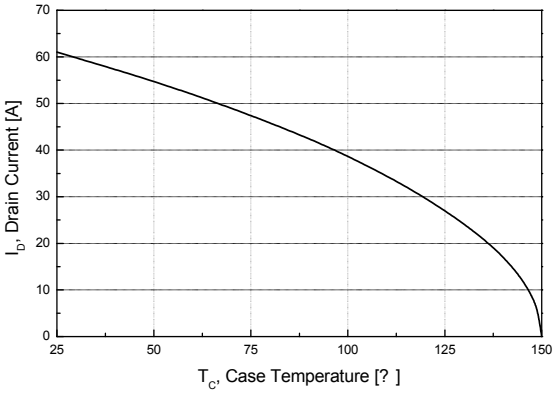
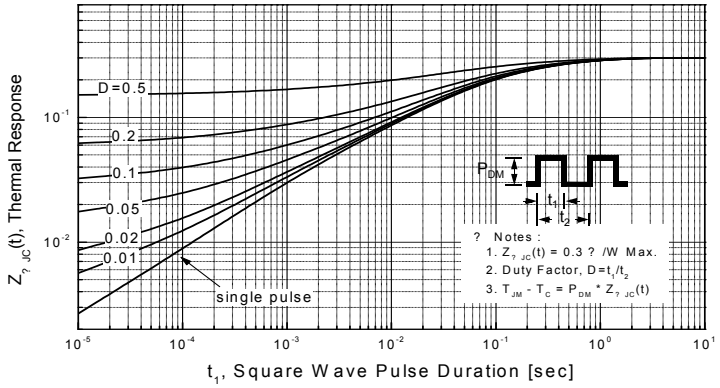
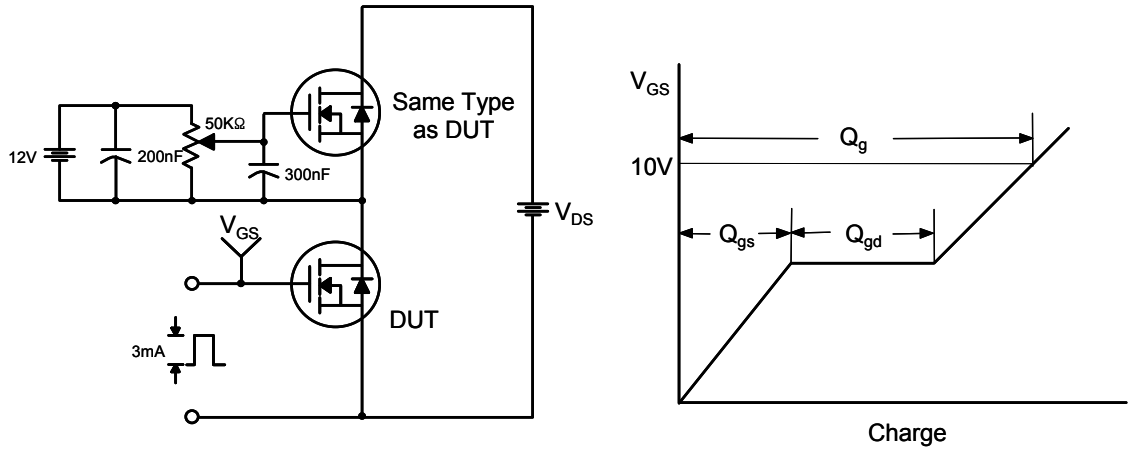


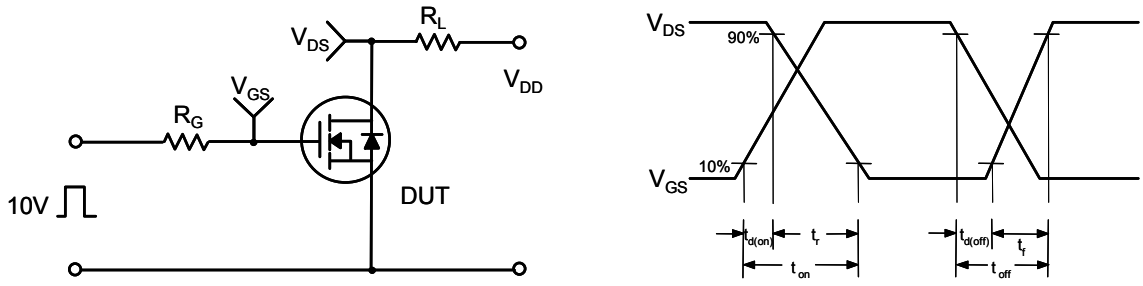
Figure 11. Transient Thermal Response Curve



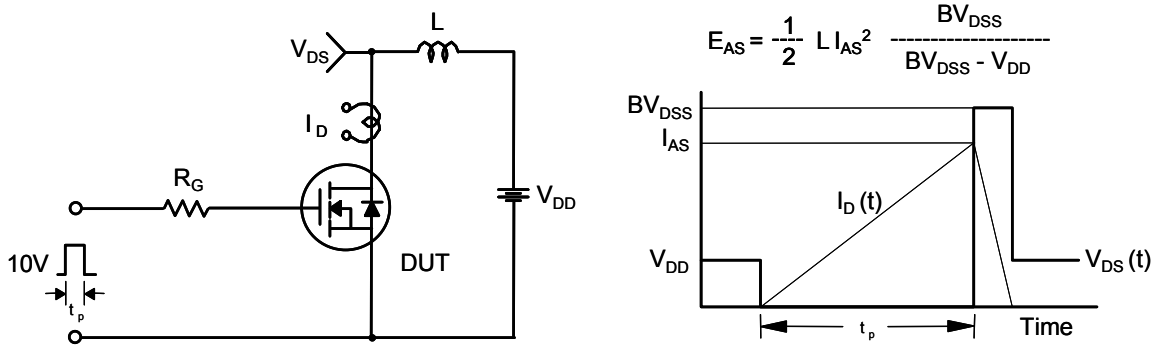
Gate Charge Test Circuit & Waveform



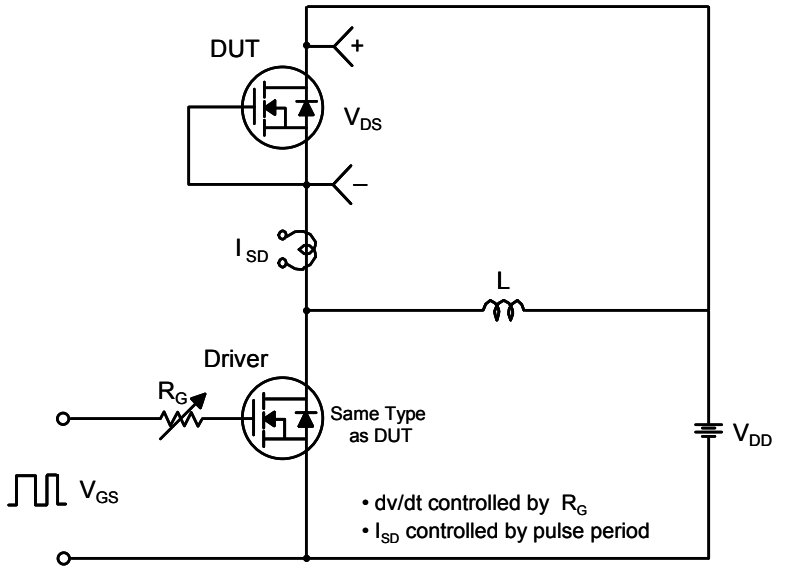
Resistive Switching Test Circuit & Waveforms

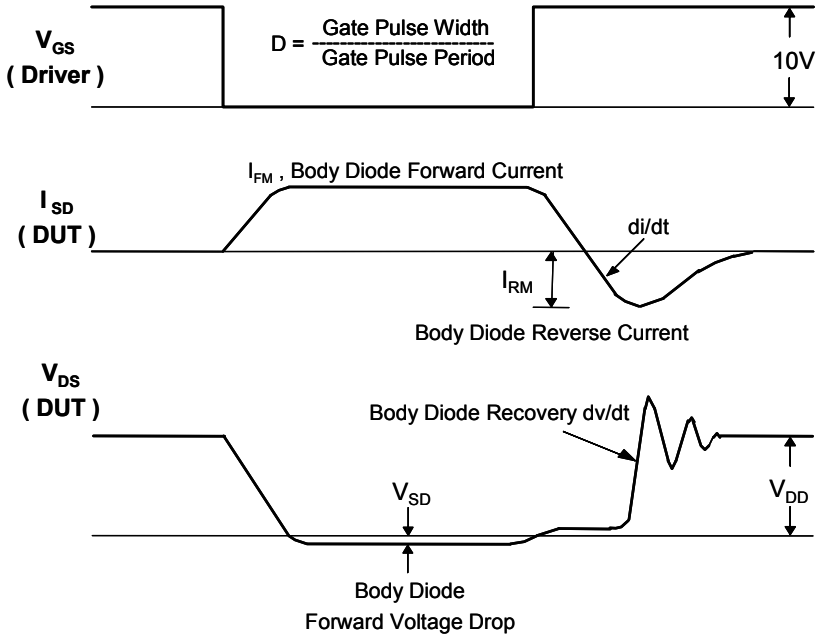


Unclamped Inductive Switching Test Circuit & Waveforms



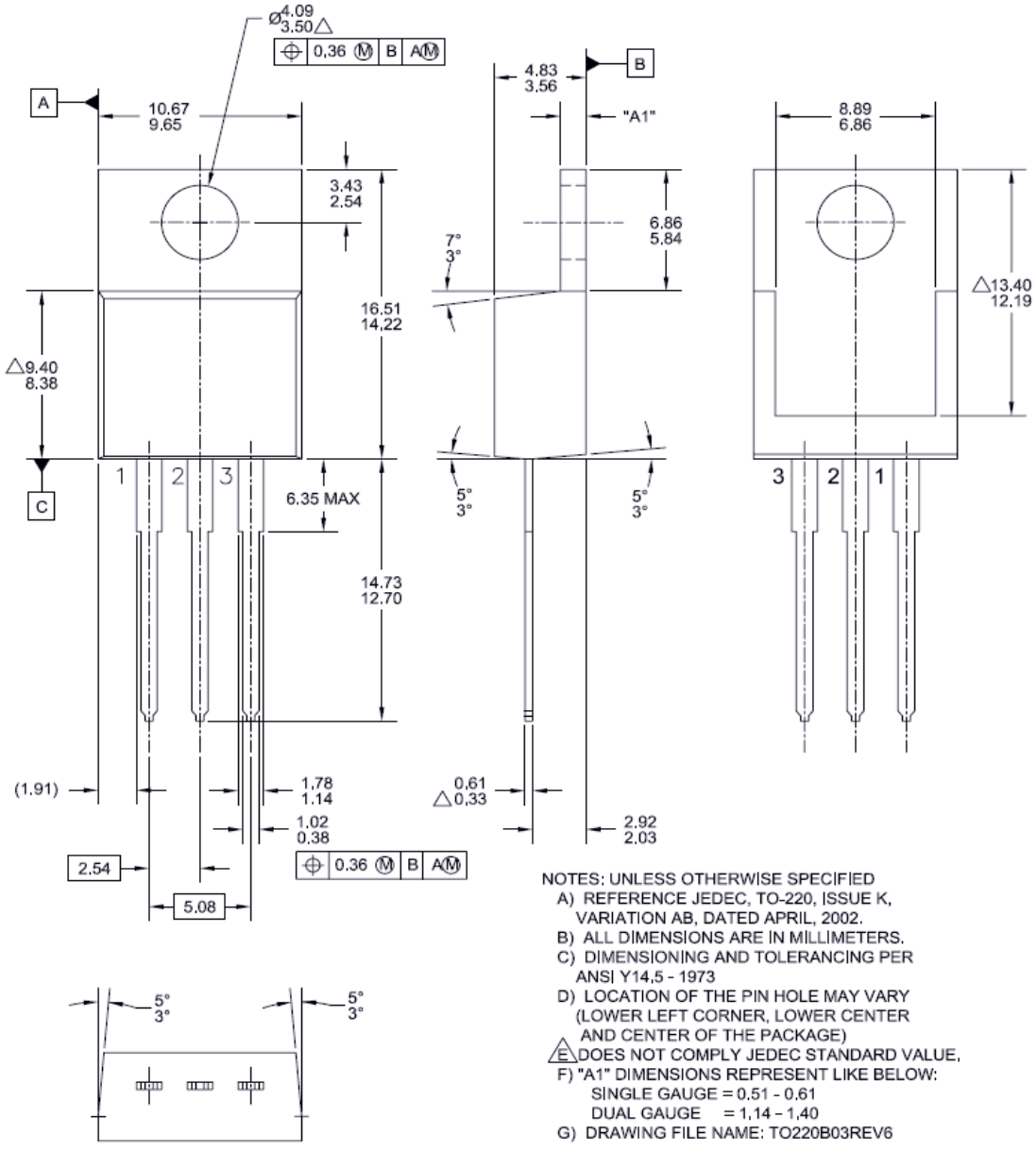
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

TO-220B03



NOTES: UNLESS OTHERWISE SPECIFIED
A) REFERENCE JEDEC, TO-220, ISSUE K, VARIATION AB, DATED APRIL, 2002.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5 - 1973
D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
△E DOES NOT COMPLY JEDEC STANDARD VALUE,
F) "A1" DIMENSIONS REPRESENT LIKE BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1,14 – 1,40
G) DRAWING FILE NAME: TO220B03REV6

Dimensions in Millimeters

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